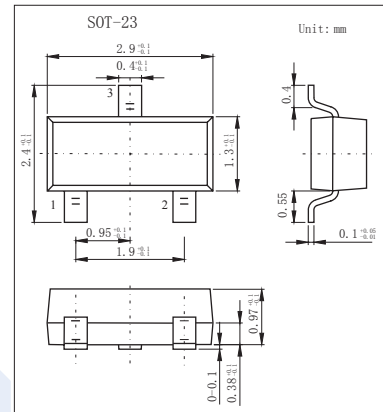
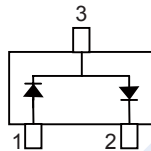


Switching Diodes

1SS226

■ Features

- Small Package
- Low forward voltage : $V_{F(3)} = 0.9$ V(Typ.)
- Fast Reverse Recovery Time : $t_{rr} = 1.6$ ns(Typ.)
- Small Total Capacitance : $C_T = 0.9$ pF(Typ.)

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Peak Reverse voltage	V_{RM}	85	V
DC Blocking Voltage	V_R	80	
Average Rectified Output Current	I_o	100	mA
Peak forward surge current	I_{FM}	300	
Power Dissipation	P_D	150	mW
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage temperature range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	V_R	$I_R = 100 \mu\text{A}$	80			V
Forward voltage	V_{F1}	$I_F = 1 \text{ mA}$		0.6		
	V_{F2}	$I_F = 10 \text{ mA}$		0.72		
	V_{F3}	$I_F = 100 \text{ mA}$		0.9	1.2	
Reverse voltage leakage current	I_{R1}	$V_R = 30 \text{ V}$			0.1	μA
	I_{R2}	$V_R = 80 \text{ V}$			0.5	
Capacitance between terminals	C_T	$V_R = 0 \text{ V}, f = 1 \text{ MHz}$		0.9	3	pF
Reverse recovery time	t_{rr}	$I_F = 10 \text{ mA}$		1.6	4	ns

■ Marking

NO.	1SS226
Marking	C3

Switching Diodes

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■ Typical Characteristics

